

FileViewEditToolsWindowHelp

Drafts

- BRS:
- BRS:
- BRS:
- BRS: knall
- BRS: 19 21 23
- BRS: 32with 33

Pending

Active

- L10: (2880230) molecu\$4 isomer\$7 organic polymer
- L11: (6146155) electric\$4 voltage potential
- L12: (2045) 10 near memory
- L13: (3253431) light radiat\$4
- L14: (185663) eras\$4
- L15: (3063) 11 with 13 with 14
- L16: (1) 12 same 15
- L17: (9) 12 and 15
- L18: (9) 17 and 14
- L19: (5455) 10 near 5 memory
- L20: (9) 19 same 15
- L21: (47) 19 and 15
- L22: (6872) (257/295,296,40,431).CCLS.
- L23: (20) 15 and 22

Failed

Saved

- S2: (1) 09/948877

DBs: US:PGPUB,USPAT,EPO,JPO,DERWENT,ISW,TDB

Default operator: OR

15 and 22

Jan 2005

FileDetailsHTML

	U	Inventor	Document#	Issue	P	Title	Current	Current XR	Retrieval	S	C	P	Image	Doc	P
1		Stasiak, Jam	US 682868	2004	2	Memory device having a semiconducting poly	257/777;257/237;							US 682868	
2		Krieger, Juri	US 2004015	2004	2	Memory device	257/40							US 200401	
3		Stasiak, Jam	US 2003023	2003	2	Memory device having a semiconducting poly	257/40							US 200302	
4		Eitan, Boaz	US 2003020	2003	2	Non-volatile electrically erasable and progra	257/296;257/E21,21							US 200302	
5		Bohmer, Mar	US 2001000	2001	6	Semiconductor device comprising a security	257/679;257/431;							US 200100	
6		Eitan, Boaz	US 6803299	2004	2	Non-volatile electrically erasable and progra	439/593;257/296;							US 680329	
7		Peng, Jack Z	US 6798693	2004	2	Semiconductor memory cell and memory arr	365/177;257/296;							US 679869	
8		Peng, Jack Z	US 6766980	2004	2	Smart card having memory using a breakdown	235/492;257/296;							US 676698	
9		Peng, Jack Z	US 6700151	2004	2	Reprogrammable non-volatile memory using a	257/299;257/253;							US 670015	
10		Jiang, Chun e	US 6600188	2003	6	EEPROM with a neutralized doping at tunnel	257/296;257/549;							US 660018	

Ready